

Part Number

Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	Wafer Vendor
	2.0	Primary Flat Orientation	{110} +/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none / Semi standard	
	5.0	Secondary Flat Length	18.50 +/- 2.50 mm	Wafer Vendor
	6.0	Overall Thickness	550.00 +/- 13.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	9.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100%
	11.0	Edge Exclusion	5mm	Guaranteed by process
	12.0	Edge Rounding	R210 (or less), 22deg bevel edge	Wafer Vendor
HandleSilicon	13.0	Handle Growth Method	CZ	Wafer Vendor
	14.0	Handle Orientation	{100} +/-1.0 degree	Wafer Vendor
	15.0	Handle Thickness	525.00 +/- 10.00 µm	ADE, 100%
	16.0	Handle Doping Type	N	Wafer Vendor
	17.0	Handle Dopant	Phosphorous	Wafer Vendor
	18.0	Handle Resistivity	1 - 10 Ohmcm	Wafer Vendor
	19.0	Backside Finish	Device layer #2	Guaranteed by Process
BuriedOxide	20.0	Oxide Type	Thermal	
	21.0	Oxide Thickness	4,000.00 +/- 200.00 A	Nanospec centre point, 4%
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	24.0	Nominal Thickness	14.00 +/- 1.00 µm	FTIR, 100% 9-Pt (note3)
	25.0	Device Doping Type	N	Wafer Vendor
	26.0	Device Dopant	Phosphorous	Wafer Vendor
	27.0	Device Resistivity	1 - 10 Ohmcm	Wafer Vendor
	28.0	Oxygen Concentration	6 - 18 ppma	Wafer Vendor
BuriedOxide2	29.0	Oxide 2 Type	Thermal	
	30.0	Oxide 2 Thickness	4,000.00 +/- 200.00 A	Nanospec centre point measurement, 4%
DeviceSilicon2	31.0	Device 2 Growth Method	CZ	Wafer Vendor
	32.0	Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	33.0	Device 2 Nominal Thickness	11.00 +/- 1.00 um	FTIR, 100% 9-point measurement (see note 3)
	34.0	Device 2 DopingType	N	Wafer Vendor
	35.0	Device 2 Dopant	Phosphorous	Wafer Vendor

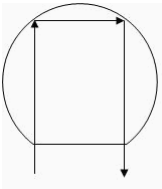
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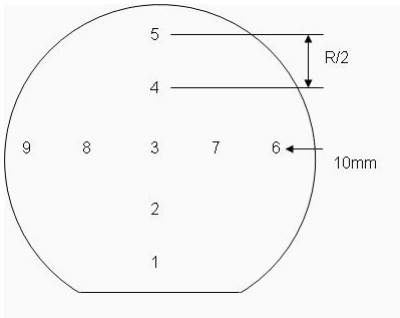
Category	Parameter		Specification	Measurement Method
DeviceSilicon2	36.0	Device 2 Resistivity	1 - 10 Ohmcm	Wafer Vendor
	37.0	Oxygen Concentration 2	6 - 18 ppma	Wafer Vendor
DeviceSilicon	38.0	Voids	none	Bright Light, 100% (note 2)
	39.0	Scratches	0	Bright Light, 100% (note 2)
	40.0	Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information